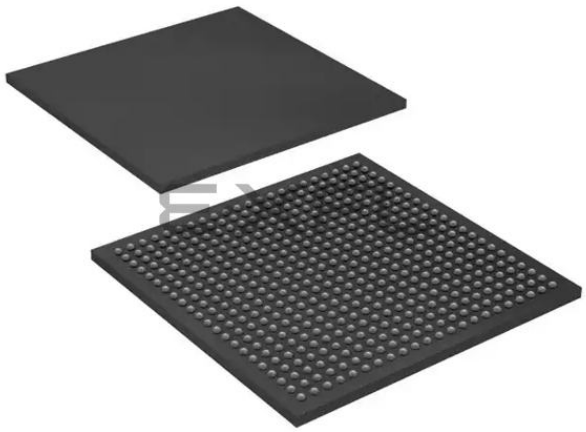

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	832
Number of Logic Elements/Cells	8320
Total RAM Bits	106496
Number of I/O	376
Number of Gates	526000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k200cf484c8es

Table 4. APEX 20KC FineLine BGA Package Options & I/O Count Notes (1), (2)			
Device	**484 Pin**	**672 Pin**	**1,020 Pin**
EP20K200C	376		
EP20K400C		488 (3)	
EP20K600C		508 (3)	588
EP20K1000C		508 (3)	708

Notes to Tables 3 and 4:

(1) I/O counts include dedicated input and clock pins.

(2) APEX 20KC device package types include plastic quad flat pack (PQFP), 1.27-mm pitch ball-grid array (BGA), and 1.00-mm pitch FineLine BGA™ packages.

(3) This device uses a thermally enhanced package, which is taller than the regular package. Consult the *Altera Device Package Information Data Sheet* for detailed package size information.

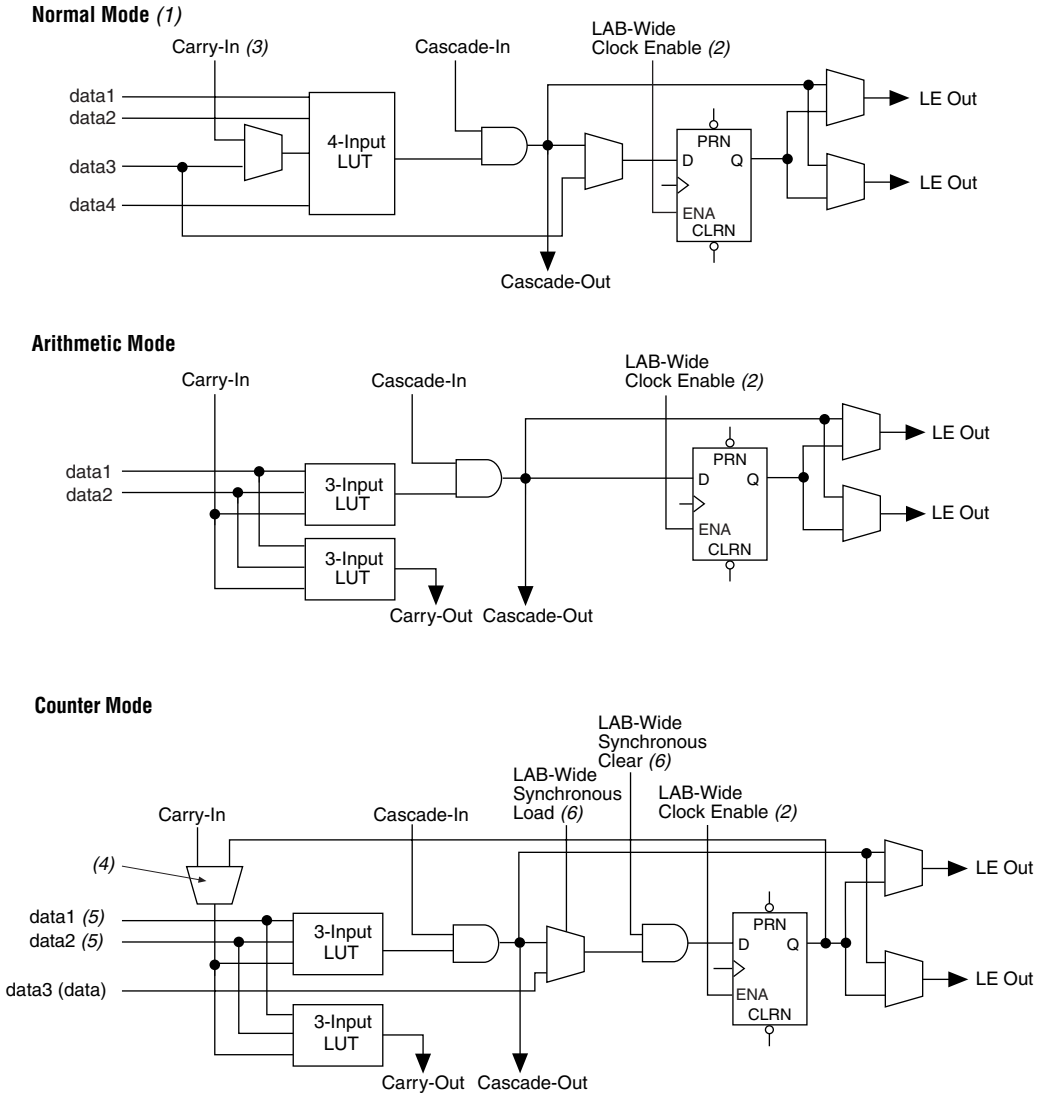
Table 5. APEX 20KC QFP & BGA Package Sizes				
Feature	**208-Pin PQFP**	**240-Pin PQFP**	**356-Pin BGA**	**652-Pin BGA**
Pitch (mm)	0.50	0.50	1.27	1.27
Area (mm^2)	924	1,218	1,225	2,025
Length × Width (mm × mm)	30.4 × 30.4	34.9 × 34.9	35.0 × 35.0	45.0 × 45.0

Table 6. APEX 20KC FineLine BGA Package Sizes			
Feature	**484 Pin**	**672 Pin**	**1,020 Pin**
Pitch (mm)	1.00	1.00	1.00
Area (mm^2)	529	729	1,089
Length × Width (mm × mm)	23 × 23	27 × 27	33 × 33

General Description

Similar to APEX 20K and APEX 20KE devices, APEX 20KC devices offer the MultiCore architecture, which combines the strengths of LUT-based and product-term-based devices with an enhanced memory structure. LUT-based logic provides optimized performance and efficiency for data-path, register-intensive, mathematical, or digital signal processing (DSP) designs. Product-term-based logic is optimized for complex combinatorial paths, such as complex state machines. LUT- and product-term-based logic combined with memory functions and a wide variety of MegaCore and AMPP functions make the APEX 20KC architecture uniquely suited for SOPC designs. Applications historically requiring a combination of LUT-, product-term-, and memory-based devices can now be integrated into one APEX 20KC device.

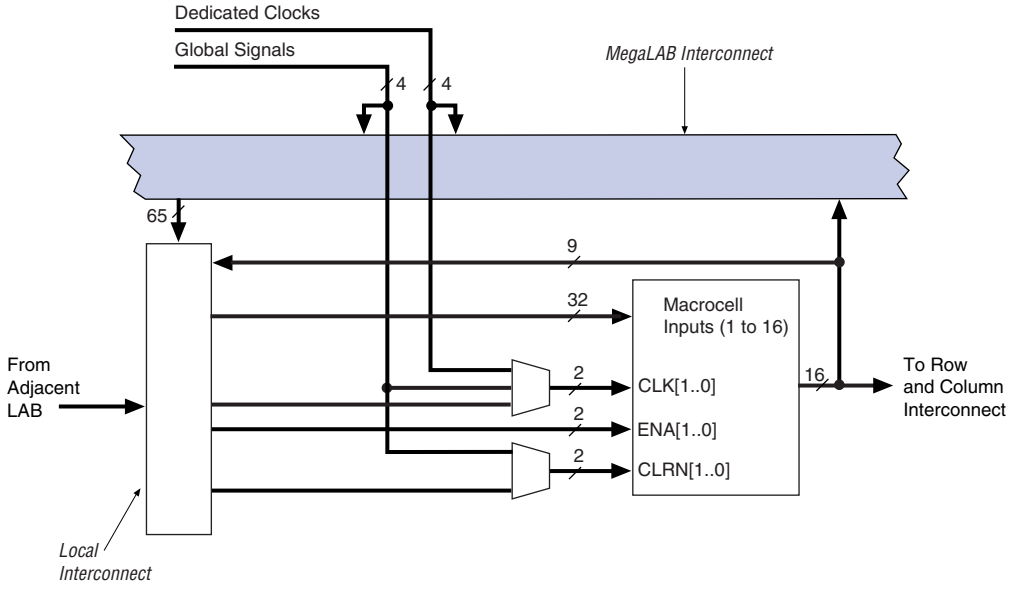
Figure 8. APEX 20KC LE Operating Modes



Notes to Figure 8:

(1) LEs in normal mode support register packing.
(2) There are two LAB-wide clock enables per LAB.
(3) When using the carry-in in normal mode, the packed register feature is unavailable.
(4) A register feedback multiplexer is available on LE1 of each LAB.
(5) The DATA1 and DATA2 input signals can supply counter enable, up or down control, or register feedback signals for LEs other than the second LE in an LAB.
(6) The LAB-wide synchronous clear and LAB wide synchronous load affect all registers in an LAB.

Figure 13. Product-Term Logic in ESB



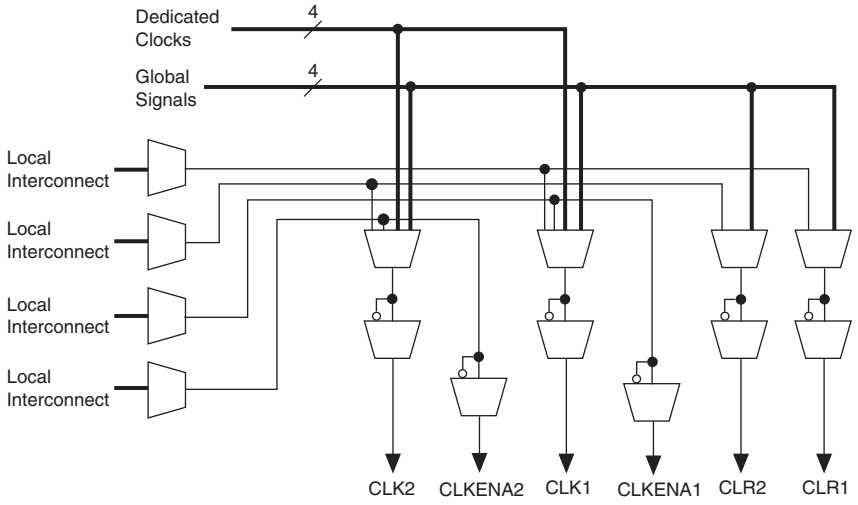
Macrocells

APEX 20KC macrocells can be configured individually for either sequential or combinatorial logic operation. The macrocell consists of three functional blocks: the logic array, the product-term select matrix, and the programmable register.

Combinatorial logic is implemented in the product terms. The product-term select matrix allocates these product terms for use as either primary logic inputs (to the OR and XOR gates) to implement combinatorial functions, or as parallel expanders to be used to increase the logic available to another macrocell. One product term can be inverted; the Quartus II software uses this feature to perform De Morgan's inversion for more efficient implementation of wide OR functions. The Quartus II Compiler can use a NOT-gate push-back technique to emulate an asynchronous preset. Figure 14 shows the APEX 20KC macrocell.

The programmable register also supports an asynchronous clear function. Within the ESB, two asynchronous clears are generated from global signals and the local interconnect. Each macrocell can either choose between the two asynchronous clear signals or choose to not be cleared. Either of the two clear signals can be inverted within the ESB. Figure 15 shows the ESB control logic when implementing product-terms.

Figure 15. ESB Product-Term Mode Control Logic



Parallel Expanders

Parallel expanders are unused product terms that can be allocated to a neighboring macrocell to implement fast, complex logic functions. Parallel expanders allow up to 32 product terms to feed the macrocell OR logic directly, with two product terms provided by the macrocell and 30 parallel expanders provided by the neighboring macrocells in the ESB.

The Quartus II Compiler can allocate up to 15 sets of up to two parallel expanders per set to the macrocells automatically. Each set of two parallel expanders incurs a small, incremental timing delay. Figure 16 shows the APEX 20KC parallel expanders.

ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the FastTrack or MegaLAB interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the FastTrack and MegaLAB interconnects. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

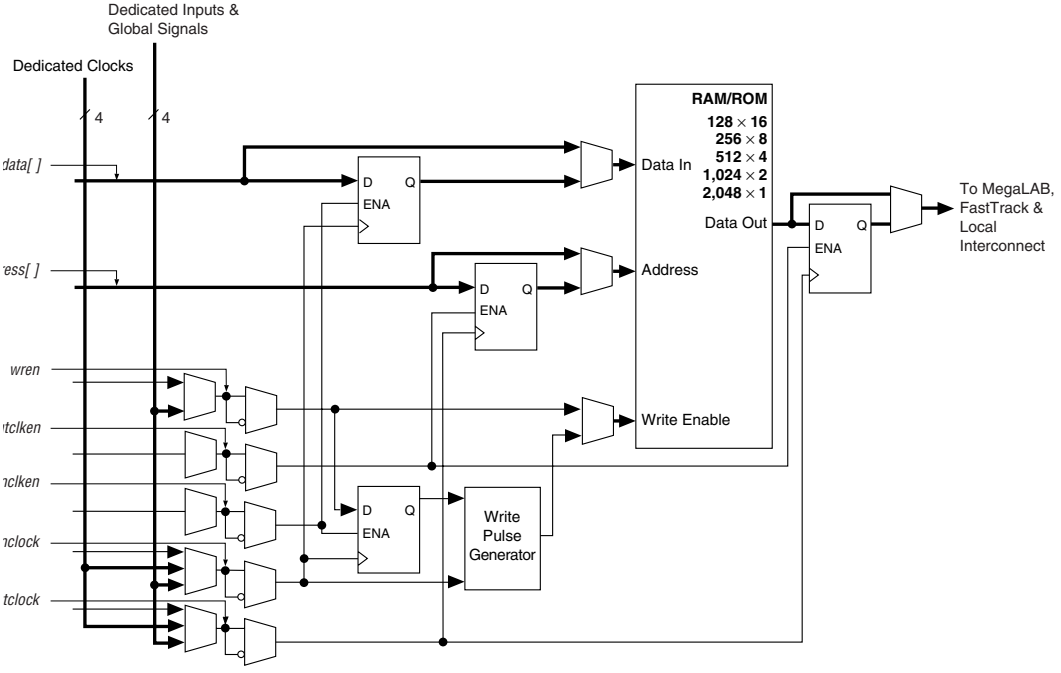
When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Read/Write Clock Mode

The read/write clock mode contains two clocks. One clock controls all registers associated with writing: data input, WE, and write address. The other clock controls all registers associated with reading: read enable (RE), read address, and data output. The ESB also supports clock enable and asynchronous clear signals; these signals also control the read and write registers independently. Read/write clock mode is commonly used for applications where reads and writes occur at different system frequencies. Figure 20 shows the ESB in read/write clock mode.

Figure 20. ESB in Read/Write Clock Mode *Note (1)*



Note to Figure 20:

(1) All registers can be cleared asynchronously by ESB local interconnect signals, global signals, or the chip-wide reset.

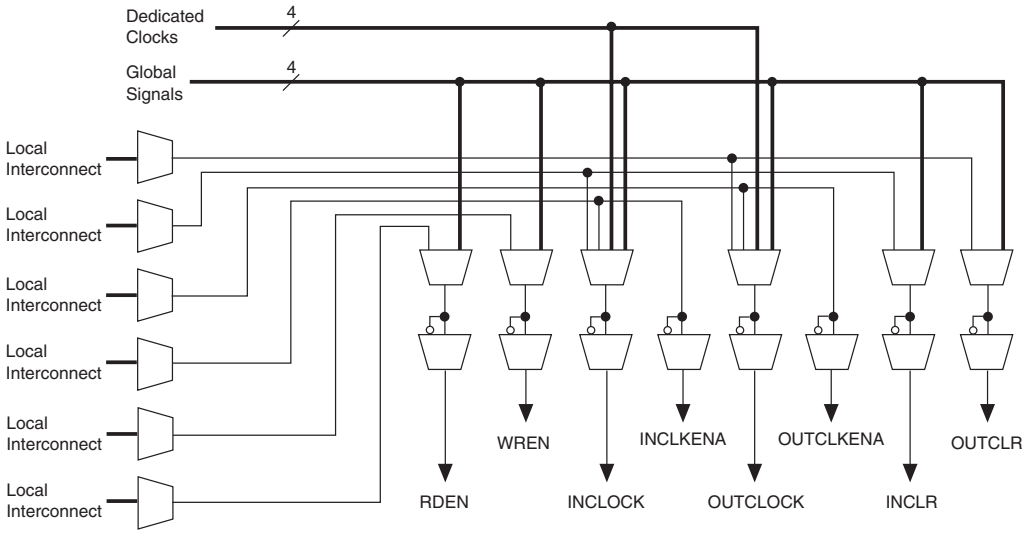
CAM is used for high-speed search operations. When searching for data within a RAM block, the search is performed serially. Thus, finding a particular data word can take many cycles. CAM searches all addresses in parallel and outputs the address storing a particular word. When a match is found, a match flag is set high. Figure 23 shows the CAM block diagram.

For more information on APEX 20KC devices and CAM, see *Application Note 119 (Implementing High-Speed Search Applications with APEX CAM).*

Driving Signals to the ESB

ESBs provide flexible options for driving control signals. Different clocks can be used for the ESB inputs and outputs. Registers can be inserted independently on the data input, data output, read address, write address, WE, and RE signals. The global signals and the local interconnect can drive the WE and RE signals. The global signals, dedicated clock pins, and local interconnect can drive the ESB clock signals. Because the LEs drive the local interconnect, the LEs can control the WE and RE signals and the ESB clock, clock enable, and asynchronous clear signals. Figure 24 shows the ESB control signal generation logic.

Figure 24. ESB Control Signal Generation

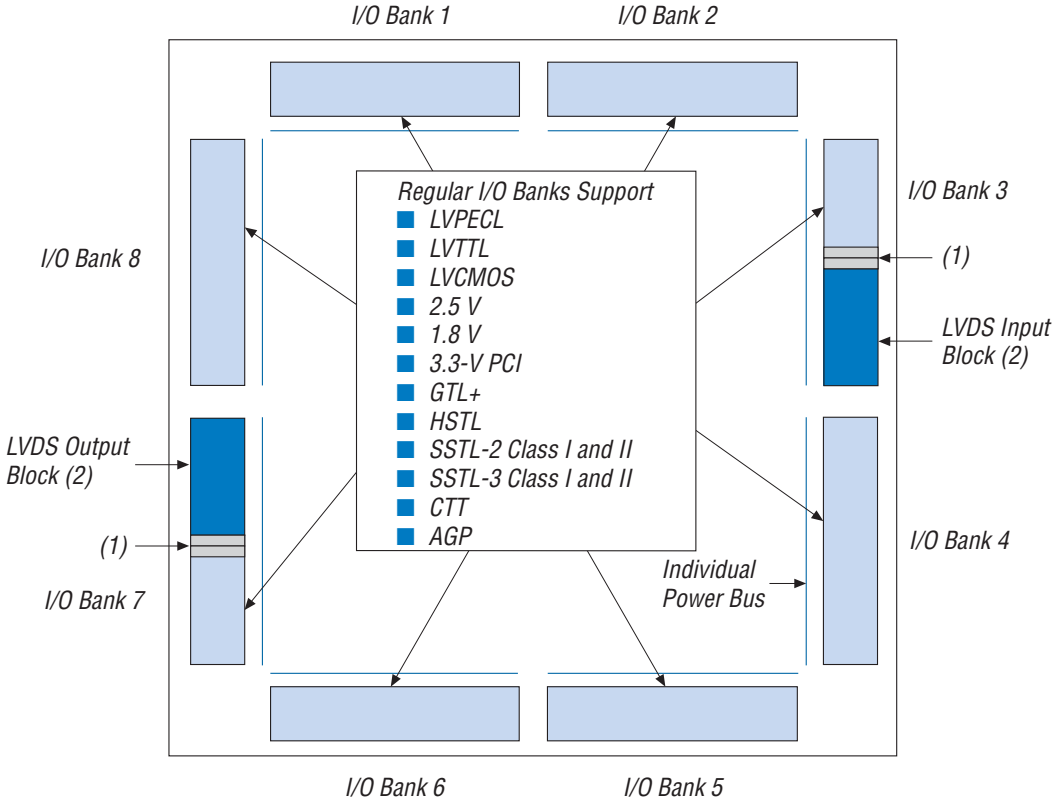


An ESB is fed by the local interconnect, which is driven by adjacent LEs (for high-speed connection to the ESB) or the MegaLAB interconnect. The ESB can drive the local, MegaLAB, or FastTrack interconnect routing structure to drive LEs and IOEs in the same MegaLAB structure or anywhere in the device.

The register in the APEX 20KC IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, an asynchronous preset can control the register. This feature is useful for cases where the APEX 20KC device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Figure 25 shows how fast bidirectional I/O pins are implemented in APEX 20KC devices. This feature is useful for cases where the APEX 20KC device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Figure 28. APEX 20KC I/O Banks



Notes to Figure 28:

(1) For more information on placing I/O pins in LVDS blocks, refer to the "Guidelines for Using LVDS Blocks" section in *Application Note 120 (Using LVDS in APEX 20KE Devices)*.

(2) If the LVDS input and output blocks are not used for LVDS, they can support all of the I/O standards and can be used as input, output, or bidirectional pins with V_{CCIO} set to 3.3 V, 2.5 V, or 1.8 V.

Power Sequencing & Hot Socketing

Because APEX 20KC devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. Therefore, the V_{CCIO} and V_{CCINT} power supplies may be powered in any order.

Table 12. APEX 20KC Clock Input & Output Parameters (Part 2 of 2) *Note (1)*

Symbol	Parameter	I/O Standard	-7 Speed Grade		-8 Speed Grade		Units
			Min	Max	Min	Max	
f_{CLOCK1_EXT}	Output clock frequency for external clock1 output	3.3-V LVTTL	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		2.5-V LVTTL	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		1.8-V LVTTL	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		GTL+	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-2 Class I	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-2 Class II	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-3 Class I	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-3 Class II	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		LVDS	*(5)*	*(5)*	*(5)*	*(5)*	MHz
f_{IN}	Input clock frequency	3.3-V LVTTL	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		2.5-V LVTTL	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		1.8-V LVTTL	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		GTL+	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-2 Class I	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-2 Class II	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-3 Class I	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-3 Class II	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		LVDS	*(5)*	*(5)*	*(5)*	*(5)*	MHz

Notes to Tables 11 and 12:

(1) All input clock specifications must be met. The PLL may not lock onto an incoming clock if the clock specifications are not met, creating an erroneous clock within the device.
(2) The maximum lock time is 40 µs or 2,000 input clock cycles, whichever occurs first.
(3) Before configuration, the PLL circuits are disable and powered down. During configuration, the PLLs remain disabled. The PLLs begin to lock once the device is in the user mode. If the clock enable feature is used, lock begins once the `CLKLK_ENA` pin goes high in user mode.
(4) The PLL VCO operating range is 200 MHz ≤ f_{VCO} ≤ 840 MHz for LVDS mode.
(5) Contact Altera Applications for information on these parameters.

SignalTap Embedded Logic Analyzer

APEX 20KC devices include device enhancements to support the SignalTap embedded logic analyzer. By including this circuitry, the APEX 20KC device provides the ability to monitor design operation over a period of time through the IEEE Std. 1149.1 (JTAG) circuitry; a designer can analyze internal logic at speed without bringing internal signals to the I/O pins. This feature is particularly important for advanced packages such as FineLine BGA packages because adding a connection to a pin during the debugging process can be difficult after a board is designed and manufactured.

Figure 30. APEX 20KC JTAG Waveforms

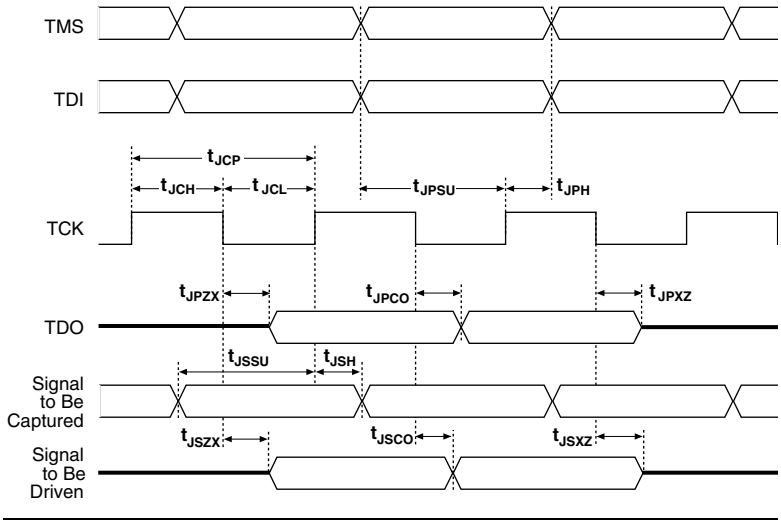


Table 16 shows the JTAG timing parameters and values for APEX 20KC devices.

Table 16. APEX 20KC JTAG Timing Parameters & Values

Symbol	Parameter	Min	Max	Unit
t_{JCP}	TCK clock period	100		ns
t_{JCH}	TCK clock high time	50		ns
t_{JCL}	TCK clock low time	50		ns
t_{JPSU}	JTAG port setup time	20		ns
t_{JPH}	JTAG port hold time	45		ns
t_{JPCO}	JTAG port clock to output		25	ns
t_{JPZX}	JTAG port high impedance to valid output		25	ns
t_{JPXZ}	JTAG port valid output to high impedance		25	ns
t_{JSSU}	Capture register setup time	20		ns
t_{JSH}	Capture register hold time	45		ns
t_{JSCO}	Update register clock to output		35	ns
t_{JSZX}	Update register high impedance to valid output		35	ns
t_{JSXZ}	Update register valid output to high impedance		35	ns

For more information, see the following documents:

- *Application Note 39 (IEEE Std. 1149.1 (JTAG) Boundary-Scan Testing in Altera Devices)*

Table 26. 3.3-V PCI-X Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	Output supply voltage		3.0	3.3	3.6	V
V_{IH}	High-level input voltage		0.5 × V_{CCIO}		V_{CCIO} + 0.5	V
V_{IL}	Low-level input voltage		–0.5		0.35 × V_{CCIO}	V
V_{IPU}	Input pull-up voltage		0.7 × V_{CCIO}			V
I_{IL}	Input pin leakage current	0 < V_{IN} < V_{CCIO}	–10.0		10.0	µA
V_{OH}	High-level output voltage	I_{OUT} = –500 µA	0.9 × V_{CCIO}			V
V_{OL}	Low-level output voltage	I_{OUT} = 1,500 µA			0.1 × V_{CCIO}	V
L_{pin}	Pin Inductance				15.0	nH

Table 27. 3.3-V LVDS I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.135	3.3	3.465	V
V_{OD}	Differential output voltage	R_L = 100 Ω	250		650	mV
Δ V_{OD}	Change in V_{OD} between high and low	R_L = 100 Ω			50	mV
V_{OS}	Output offset voltage	R_L = 100 Ω	1.125	1.25	1.375	V
Δ V_{OS}	Change in V_{OS} between high and low	R_L = 100 Ω			50	mV
V_{TH}	Differential input threshold	V_{CM} = 1.2 V	–100		100	mV
V_{IN}	Receiver input voltage range		0.0		2.4	V
R_L	Receiver differential input resistor (external to APEX devices)		90	100	110	Ω

Table 34. 3.3-V AGP I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.15	3.3	3.45	V
V_{REF}	Reference voltage		0.39 × V_{CCIO}		0.41 × V_{CCIO}	V
V_{IH}	High-level input voltage		0.5 × V_{CCIO}		V_{CCIO} + 0.5	V
V_{IL}	Low-level input voltage				0.3 × V_{CCIO}	V
V_{OH}	High-level output voltage	I_{OUT} = –500 µA	0.9 × V_{CCIO}		3.6	V
V_{OL}	Low-level output voltage	I_{OUT} = 1,500 µA			0.1 × V_{CCIO}	V
I_I	Input pin leakage current	0 < V_{IN} < V_{CCIO}	–10		10	µA

Table 35. CTT I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}/V_{REF} *(3)*	Termination and reference voltage		1.35	1.5	1.65	V
V_{IH}	High-level input voltage		V_{REF} + 0.2			V
V_{IL}	Low-level input voltage				V_{REF} – 0.2	V
I_I	Input pin leakage current	0 < V_{IN} < V_{CCIO}	–10		10	µA
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(1)*	V_{REF} + 0.4			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(2)*			V_{REF} – 0.4	V
I_O	Output leakage current (when output is high Z)	GND ≤ V_{OUT} ≤ V_{CCIO}	–10		10	µA

Notes to Tables 21 through 35:

(1) The I_{OH} parameter refers to high-level output current.
(2) The I_{OL} parameter refers to low-level output current. This parameter applies to open-drain pins as well as output pins.
(3) V_{REF} specifies center point of switching range.

Figure 31 shows the output drive characteristics of APEX 20KC devices.

Figure 34. ESB Synchronous Timing Waveforms

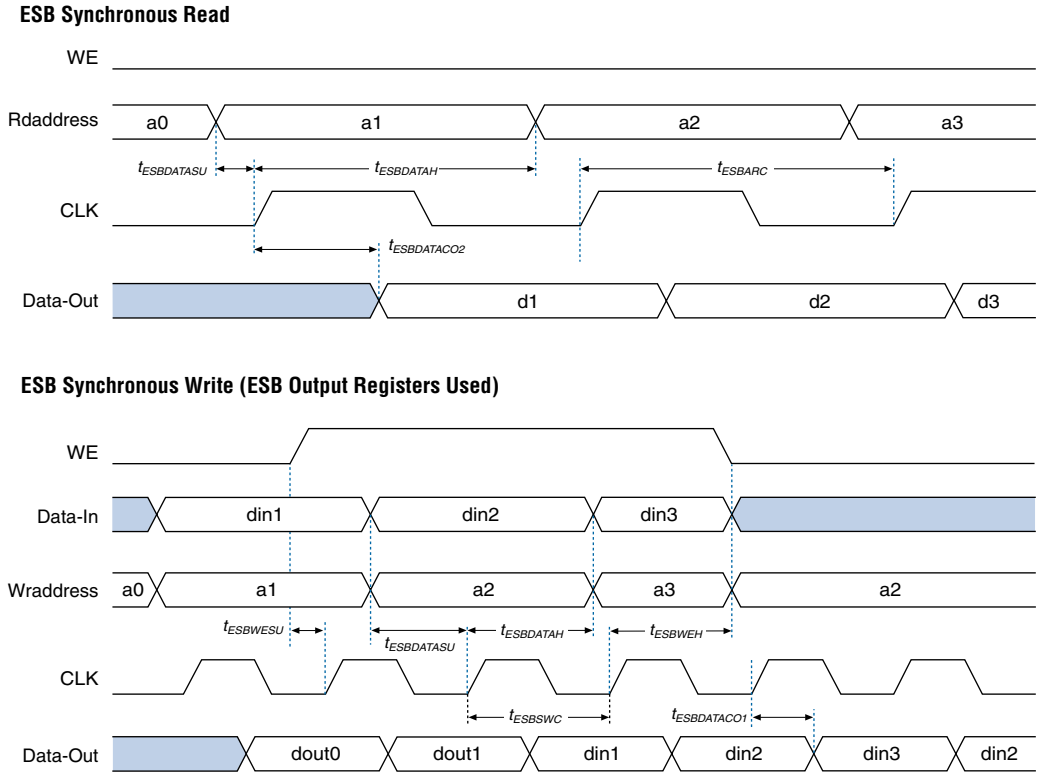


Figure 35 shows the timing model for bidirectional I/O pin timing.

Figure 36. AC Test Conditions for LVTTL, 2.5 V, 1.8 V, PCI & GTL+ I/O Standards

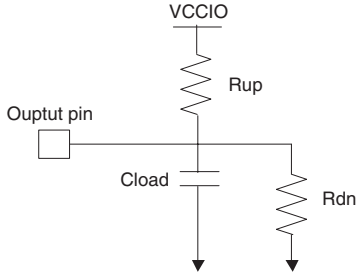


Figure 37. AC Test Conditions for SSTL-3 Class I & II I/O Standards

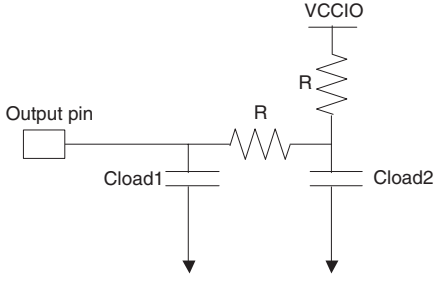


Figure 38. AC Test Conditions for the LVDS I/O Standard

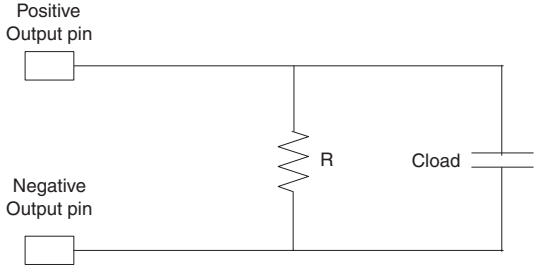


Table 46. EP20K200C f_{MAX} Routing Delays

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.15		0.17		0.20	ns
t_{F5-20}		0.81		0.94		1.12	ns
t_{F20+}		0.98		1.13		1.35	ns

Table 47. EP20K200C Minimum Pulse Width Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.33		1.66		2.00		ns
t_{CL}	1.33		1.66		2.00		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.33		1.66		2.00		ns
t_{ESBCL}	1.33		1.66		2.00		ns
t_{ESBWP}	1.05		1.28		1.44		ns
t_{ESBRP}	0.87		1.06		1.19		ns

Table 48. EP20K200C External Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.23		1.26		1.33		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	3.79	2.00	4.31	2.00	4.70	ns
$t_{INSUPLL}$	0.81		0.92		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.36	0.50	2.62	-	-	ns

Table 49. EP20K200C External Bidirectional Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	1.38		1.78		1.99		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	3.79	2.00	4.31	2.00	4.70	ns
$t_{XZBIDIR}$		6.12		6.51		7.89	ns
$t_{ZXBIDIR}$		6.12		6.51		7.89	ns
$t_{INSUBIDIRPLL}$	2.82		3.47		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.36	0.50	2.62	-	-	ns
$t_{XZBIDIRPLL}$		4.69		4.82		-	ns
$t_{ZXBIDIRPLL}$		4.69		4.82		-	ns

Table 50. EP20K400C f_{MAX} LE Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.01		0.01		0.01		ns
t_{H}	0.10		0.10		0.10		ns
t_{CO}		0.27		0.30		0.32	ns
t_{LUT}		0.65		0.78		0.92	ns

Table 59. EP20K600C Minimum Pulse Width Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.33		1.66		2.00		ns
t_{CL}	1.33		1.66		2.00		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.33		1.66		2.00		ns
t_{ESBCL}	1.33		1.66		2.00		ns
t_{ESBWP}	1.05		1.28		1.44		ns
t_{ESBRP}	0.87		1.06		1.19		ns

Table 60. EP20K600C External Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.28		1.40		1.45		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	4.29	2.00	4.77	2.00	5.11	ns
$t_{INSUPLL}$	0.80		0.91		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.37	0.50	2.63	-	-	ns

Table 63. EP20K1000C f_{MAX} ESB Timing Microparameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.48		1.57		1.65	ns
t_{ESBSRC}		2.36		2.50		2.73	ns
t_{ESBAWC}		2.93		3.46		3.86	ns
t_{ESBSWC}		3.08		3.43		3.83	ns
$t_{ESBWASU}$	0.51		0.50		0.52		ns
t_{ESBWAH}	0.38		0.51		0.57		ns
$t_{ESBWDSU}$	0.62		0.62		0.66		ns
t_{ESBWDH}	0.38		0.51		0.57		ns
$t_{ESBRASU}$	1.40		1.47		1.53		ns
t_{ESBRAH}	0.00		0.07		0.18		ns
$t_{ESBWESU}$	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	1.92		2.19		2.35		ns
$t_{ESBWADDRSU}$	–0.20		–0.28		–0.32		ns
$t_{ESBRADDRSU}$	0.00		–0.03		–0.05		ns
$t_{ESBDATACO1}$		1.12		1.30		1.46	ns
$t_{ESBDATACO2}$		2.11		2.53		2.84	ns
t_{ESBDD}		2.56		2.96		3.30	ns
t_{PD}		1.49		1.79		2.02	ns
$t_{PTERMSU}$	0.61		0.69		0.77		ns
$t_{PTERMCO}$		1.13		1.32		1.48	ns

Table 64. EP20K1000C f_{MAX} Routing Delays

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.15		0.17		0.19	ns
t_{F5-20}		1.13		1.31		1.50	ns
t_{F20+}		2.30		2.71		3.19	ns